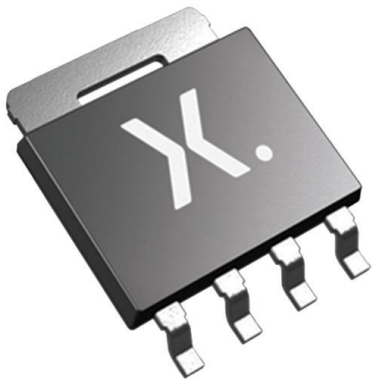


PSMN4R0-30YLDX Datasheet

www.digi-electronics.com



<https://www.DiGi-Electronics.com>

DiGi Electronics Part Number	PSMN4R0-30YLDX-DG
Manufacturer	Nexperia USA Inc.
Manufacturer Product Number	PSMN4R0-30YLDX
Description	MOSFET N-CH 30V 95A LFPAK56
Detailed Description	N-Channel 30 V 95A (Tc) 64W (Tc) Surface Mount LF PAK56, Power-SO8



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.

Purchase and inquiry

Manufacturer Product Number:

PSMN4R0-30YLDX

Series:

TrenchMOS™

FET Type:

N-Channel

Drain to Source Voltage (Vdss):

30 V

Drive Voltage (Max Rds On, Min Rds On):

4.5V, 10V

Vgs(th) (Max) @ Id:

2.2V @ 1mA

Vgs (Max):

±20V

FET Feature:

-

Operating Temperature:

-55°C ~ 175°C (Tj)

Supplier Device Package:

LFPAK56, Power-SO8

Base Product Number:

PSMN4R0

Manufacturer:

Nexperia USA Inc.

Product Status:

Active

Technology:

MOSFET (Metal Oxide)

Current - Continuous Drain (Id) @ 25°C:

95A (Tc)

Rds On (Max) @ Id, Vgs:

4mOhm @ 25A, 10V

Gate Charge (Qg) (Max) @ Vgs:

19.4 nC @ 10 V

Input Capacitance (Ciss) (Max) @ Vds:

1272 pF @ 15 V

Power Dissipation (Max):

64W (Tc)

Mounting Type:

Surface Mount

Package / Case:

SC-100, SOT-669

Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.29.0095

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99



PSMN4R0-30YLD

N-channel 30 V, 4.0 mΩ logic level MOSFET in LFPAK56
using NextPowerS3 Technology

10 October 2013

Product data sheet

1. General description

Logic level gate drive N-channel enhancement mode MOSFET in LFPAK56 package. NextPowerS3 portfolio utilising Nexperia's unique "SchottkyPlus" technology delivers high efficiency, low spiking performance usually associated with MOSFETs with an integrated Schottky or Schottky-like diode but without problematic high leakage current. NextPowerS3 is particularly suited to high efficiency applications at high switching frequencies.

2. Features and benefits

- Ultra low Q_G , Q_{GD} and Q_{OSS} for high system efficiency, especially at higher switching frequencies
- Superfast switching with soft-recovery; s-factor > 1
- Low spiking and ringing for low EMI designs
- Unique "SchottkyPlus" technology; Schottky-like performance with < 1 μA leakage at 25 °C
- Optimised for 4.5 V gate drive
- Low parasitic inductance and resistance
- High reliability clip bonded and solder die attach Power SO8 package; no glue, no wire bonds, qualified to 175 °C
- Wave solderable; exposed leads for optimal visual solder inspection

3. Applications

- On-board DC-to-DC solutions for server and telecommunications
- Secondary-side synchronous rectification in telecommunication applications
- Voltage regulator modules (VRM)
- Point-of-Load (POL) modules
- Power delivery for V-core, ASIC, DDR, GPU, VGA and system components
- Brushed and brushless motor control

4. Quick reference data

Table 1. Quick reference data

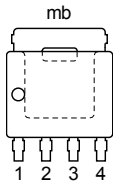
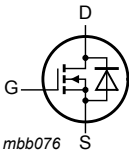
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T_j ≤ 175 °C	-	-	30	V
I_D	drain current	$T_{mb} = 25$ °C; $V_{GS} = 10$ V; Fig. 1	-	-	95	A
P_{tot}	total power dissipation	$T_{mb} = 25$ °C; Fig. 2	-	-	64	W

N-channel 30 V, 4.0 mΩ logic level MOSFET in LFAK56 using NextPowerS3 Technology

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_j	junction temperature		-55	-	175	°C
Static characteristics						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 4.5\text{ V}; I_D = 25\text{ A}; T_j = 25\text{ °C};$ Fig. 10	-	4.4	5.5	mΩ
		$V_{GS} = 10\text{ V}; I_D = 25\text{ A}; T_j = 25\text{ °C};$ Fig. 10	-	3.4	4	mΩ
Dynamic characteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 4.5\text{ V}; I_D = 25\text{ A}; V_{DS} = 15\text{ V};$ Fig. 12; Fig. 13	-	2.4	-	nC
$Q_{G(tot)}$	total gate charge	$V_{GS} = 4.5\text{ V}; I_D = 25\text{ A}; V_{DS} = 15\text{ V};$ Fig. 12; Fig. 13	-	9.1	-	nC
Source-drain diode						
S	softness factor	$I_S = 25\text{ A}; V_{GS} = 0\text{ V}; di_S/dt = -100\text{ A}/\mu\text{s};$ $V_{DS} = 15\text{ V};$ Fig. 16	-	1.1	-	

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	 <p>LFAK56; Power-SO8 (SOT669)</p>	
2	S	source		
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN4R0-30YLD	LFAK56; Power-SO8	Plastic single-ended surface-mounted package (LFAK56; Power-SO8); 4 leads	SOT669

7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN4R0-30YLD	4D030L

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$		-	30	V
V_{DGR}	drain-gate voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$; $R_{GS} = 20\text{ k}\Omega$		-	30	V
V_{GS}	gate-source voltage			-20	20	V
I_D	drain current	$V_{GS} = 10\text{ V}$; $T_{mb} = 25\text{ °C}$; Fig. 1		-	95	A
		$V_{GS} = 10\text{ V}$; $T_{mb} = 100\text{ °C}$; Fig. 1		-	67	A
I_{DM}	peak drain current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$; $T_{mb} = 25\text{ °C}$; Fig. 3		-	378	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; Fig. 2		-	64	W
T_{stg}	storage temperature			-55	175	°C
T_j	junction temperature			-55	175	°C
$T_{sld(M)}$	peak soldering temperature			-	260	°C
V_{ESD}	electrostatic discharge voltage	HBM		375	-	V
Source-drain diode						
I_S	source current	$T_{mb} = 25\text{ °C}$		-	54	A
I_{SM}	peak source current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$; $T_{mb} = 25\text{ °C}$		-	378	A
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}$; $T_{j(\text{init})} = 25\text{ °C}$; $I_D = 25\text{ A}$; $V_{sup} \leq 30\text{ V}$; $R_{GS} = 50\text{ }\Omega$; unclamped; $t_p = 129\text{ }\mu\text{s}$	[1]	-	63	mJ

[1] Protected by 100% test

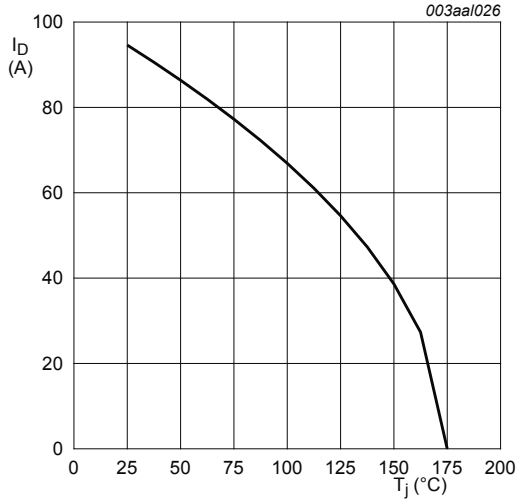


Fig. 1. Continuous drain current as a function of mounting base temperature

$$V_{GS} \geq 10V$$

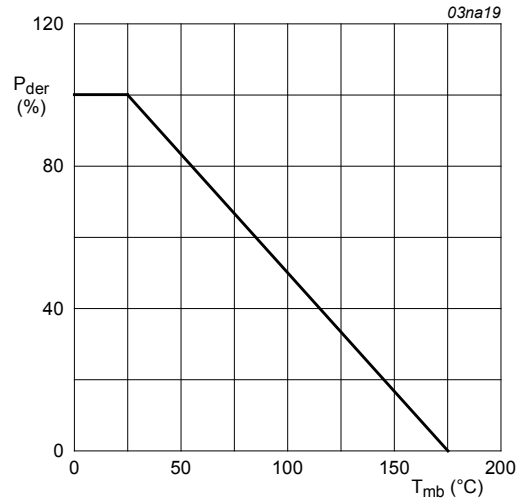


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

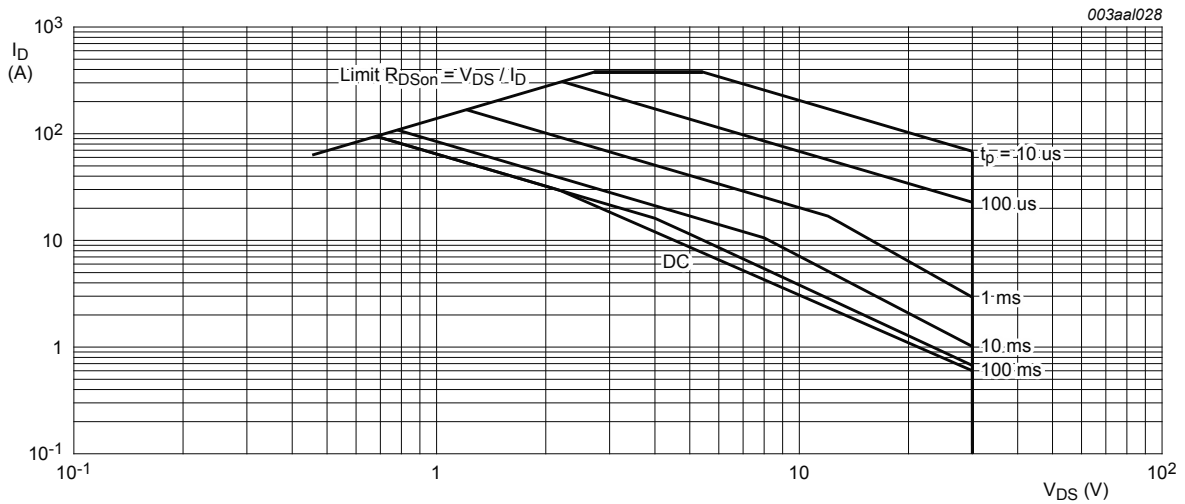


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

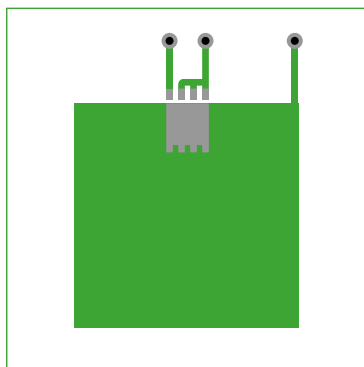
$$T_{mb} = 25^{\circ}C; I_{DM} \text{ is a single pulse}$$

9. Thermal characteristics

Table 6. Thermal characteristics

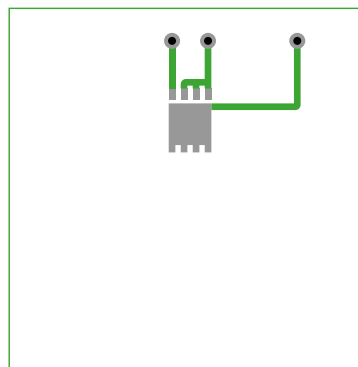
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 6	-	2.14	2.33	K/W

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	Fig. 4	-	50	-	K/W
		Fig. 5	-	125	-	K/W



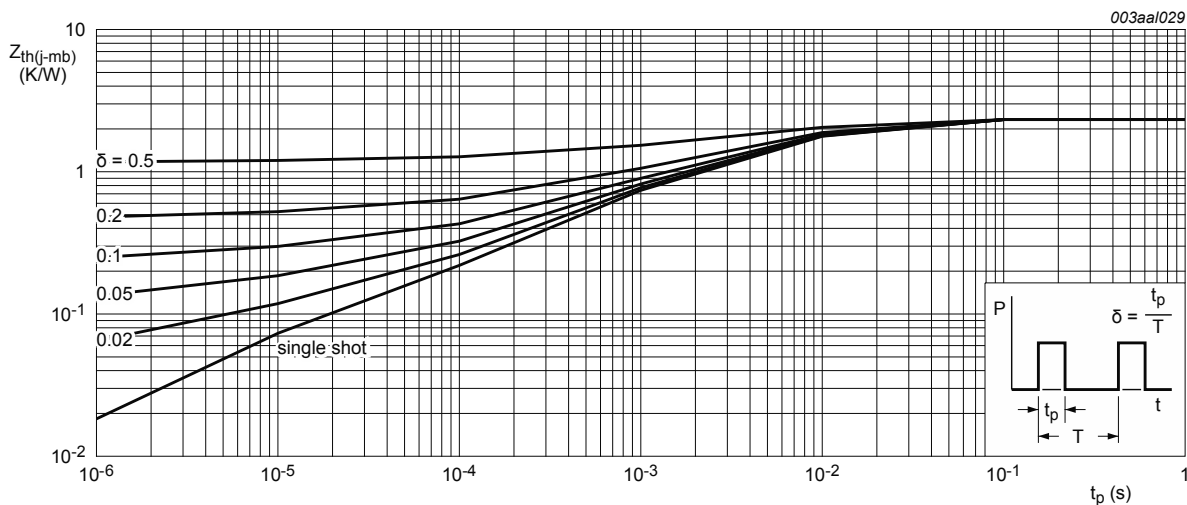
aaa-005750

Fig. 4. PCB layout for thermal resistance junction to ambient 1" square pad; FR4 Board; 2oz copper



aaa-005751

Fig. 5. PCB layout for thermal resistance junction to ambient minimum footprint; FR4 Board; 2oz copper



003aal029

Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_J = 25 \text{ }^\circ C$	30	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_J = -55 \text{ }^\circ C$	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_J = 25 \text{ }^\circ C$	1.2	1.74	2.2	V

N-channel 30 V, 4.0 mΩ logic level MOSFET in LPAK56 using NextPowerS3 Technology

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$\Delta V_{GS(th)}/\Delta T$	gate-source threshold voltage variation with temperature	$25\text{ }^{\circ}\text{C} < T_j < 150\text{ }^{\circ}\text{C}$	-	-4.1	-	mV/K
I_{DSS}	drain leakage current	$V_{DS} = 24\text{ V}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^{\circ}\text{C}$	-	-	1	μA
		$V_{DS} = 24\text{ V}; V_{GS} = 0\text{ V}; T_j = 150\text{ }^{\circ}\text{C}$	-	-	100	μA
I_{GSS}	gate leakage current	$V_{GS} = 16\text{ V}; V_{DS} = 0\text{ V}; T_j = 25\text{ }^{\circ}\text{C}$	-	-	100	nA
		$V_{GS} = -16\text{ V}; V_{DS} = 0\text{ V}; T_j = 25\text{ }^{\circ}\text{C}$	-	-	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 4.5\text{ V}; I_D = 25\text{ A}; T_j = 25\text{ }^{\circ}\text{C};$ Fig. 10	-	4.4	5.5	mΩ
		$V_{GS} = 4.5\text{ V}; I_D = 25\text{ A}; T_j = 150\text{ }^{\circ}\text{C};$ Fig. 11; Fig. 10	-	-	9.1	mΩ
		$V_{GS} = 10\text{ V}; I_D = 25\text{ A}; T_j = 25\text{ }^{\circ}\text{C};$ Fig. 10	-	3.4	4	mΩ
		$V_{GS} = 10\text{ V}; I_D = 25\text{ A}; T_j = 150\text{ }^{\circ}\text{C};$ Fig. 11; Fig. 10	-	-	6.6	mΩ
R_G	gate resistance	$f = 1\text{ MHz}$	-	2.2	-	Ω
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$I_D = 25\text{ A}; V_{DS} = 15\text{ V}; V_{GS} = 10\text{ V};$ Fig. 12; Fig. 13	-	19.4	-	nC
		$I_D = 25\text{ A}; V_{DS} = 15\text{ V}; V_{GS} = 4.5\text{ V};$ Fig. 12; Fig. 13	-	9.1	-	nC
		$I_D = 0\text{ A}; V_{DS} = 0\text{ V}; V_{GS} = 10\text{ V}$	-	18.2	-	nC
Q_{GS}	gate-source charge	$I_D = 25\text{ A}; V_{DS} = 15\text{ V}; V_{GS} = 4.5\text{ V};$ Fig. 12; Fig. 13	-	2.6	-	nC
$Q_{GS(th)}$	pre-threshold gate-source charge		-	1.9	-	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge		-	0.7	-	nC
Q_{GD}	gate-drain charge		-	2.4	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$I_D = 25\text{ A}; V_{DS} = 15\text{ V};$ Fig. 12; Fig. 13	-	2.3	-	V
C_{iss}	input capacitance	$V_{DS} = 15\text{ V}; V_{GS} = 0\text{ V}; f = 1\text{ MHz};$ $T_j = 25\text{ }^{\circ}\text{C};$ Fig. 14	-	1272	-	pF
C_{oss}	output capacitance		-	812	-	pF
C_{rss}	reverse transfer capacitance		-	87	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 15\text{ V}; R_L = 0.6\text{ }^{\Omega}; V_{GS} = 4.5\text{ V};$ $R_{G(ext)} = 5\text{ }^{\Omega}$	-	10.7	-	ns
t_r	rise time		-	21.2	-	ns
$t_{d(off)}$	turn-off delay time		-	14.9	-	ns
t_f	fall time		-	11.7	-	ns

**N-channel 30 V, 4.0 mΩ logic level MOSFET in LPAK56 using
NextPowerS3 Technology**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
Q_{oss}	output charge	$V_{GS} = 0\text{ V}$; $V_{DS} = 15\text{ V}$; $f = 1\text{ MHz}$; $T_j = 25\text{ °C}$	-	16	-	nC	
Source-drain diode							
V_{SD}	source-drain voltage	$I_S = 15\text{ A}$; $V_{GS} = 0\text{ V}$; $T_j = 25\text{ °C}$; Fig. 15	-	0.82	1.2	V	
t_{rr}	reverse recovery time	$I_S = 25\text{ A}$; $di_S/dt = -100\text{ A}/\mu\text{s}$; $V_{GS} = 0\text{ V}$; $V_{DS} = 15\text{ V}$; Fig. 16	-	25.1	-	ns	
Q_r	recovered charge		[1]	-	13.3	-	nC
t_a	reverse recovery rise time		-	-	11.9	-	ns
t_b	reverse recovery fall time		-	-	13.1	-	ns
S	softness factor		-	-	1.1	-	

[1] includes capacitive recovery

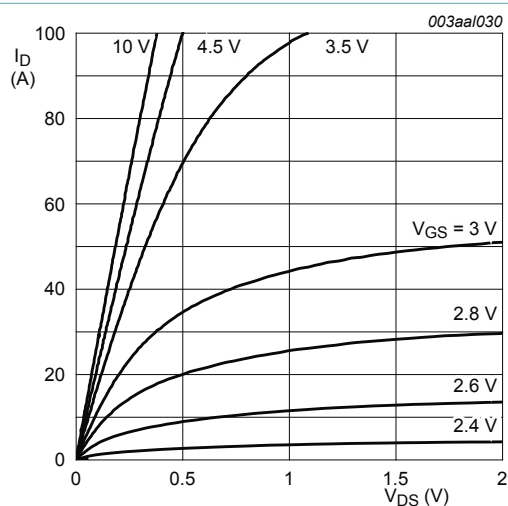


Fig. 7. Output characteristics; drain current as a function of drain-source voltage; typical values

$T_j = 25\text{ °C}$

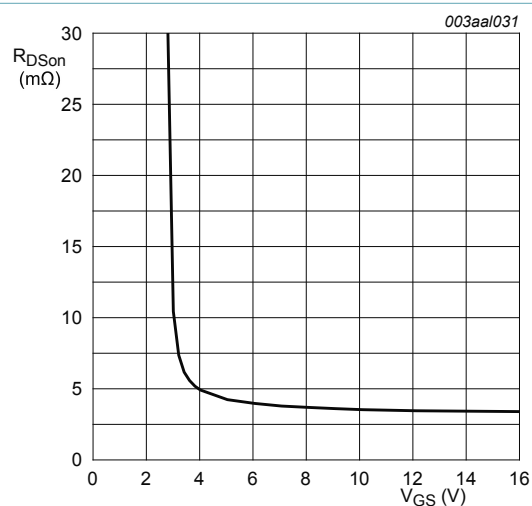


Fig. 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

$T_j = 25\text{ °C}$; $I_D = 25\text{ A}$

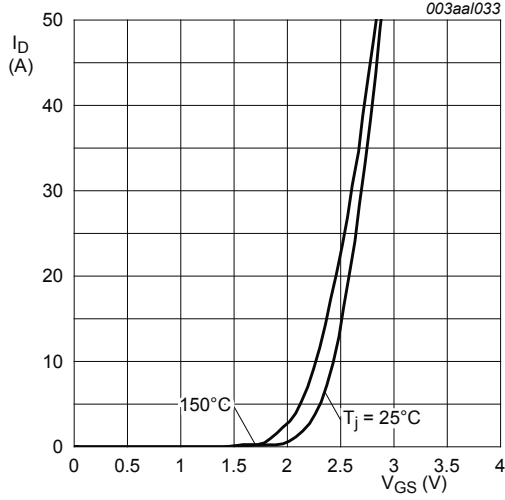


Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

$$V_{DS} = 12V$$

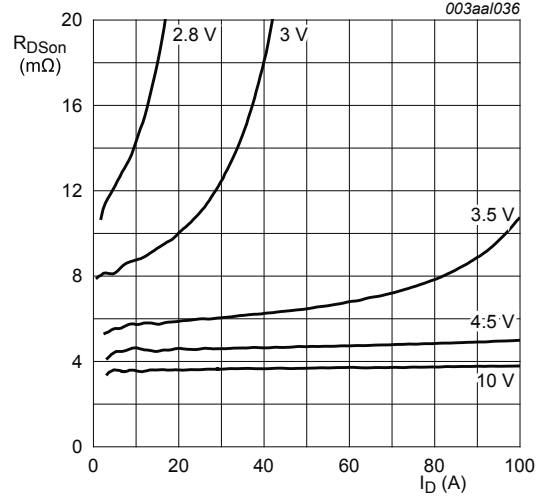


Fig. 10. Drain-source on-state resistance as a function of drain current; typical values

$$T_j = 25^\circ C$$

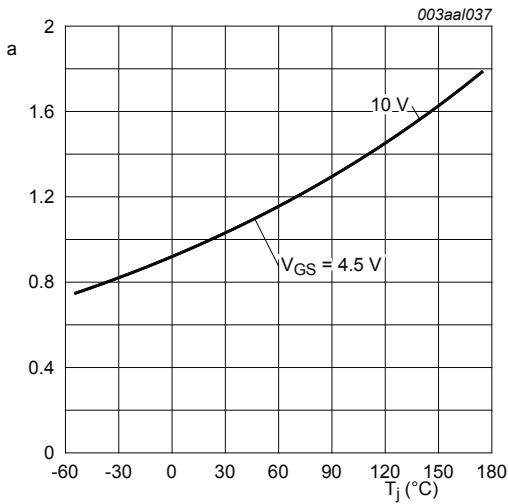


Fig. 11. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon}(25^\circ C)}$$

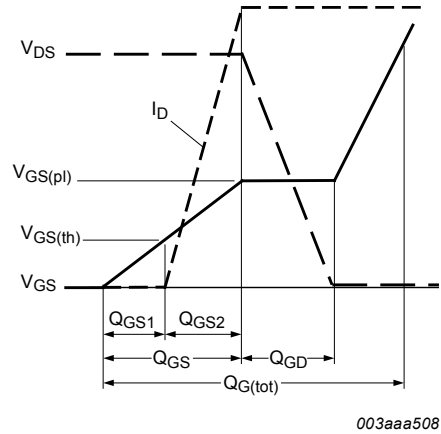


Fig. 12. Gate charge waveform definitions

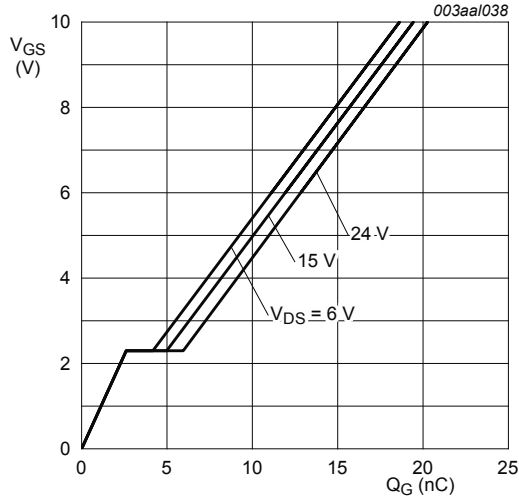


Fig. 13. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25^\circ\text{C}; I_D = 25\text{A}$$

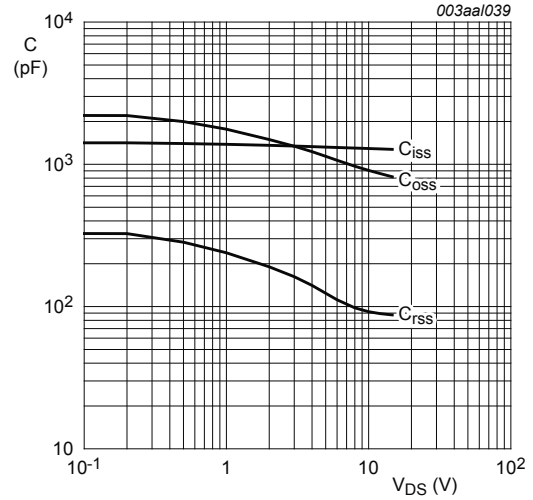


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0\text{V}; f = 1\text{MHz}$$

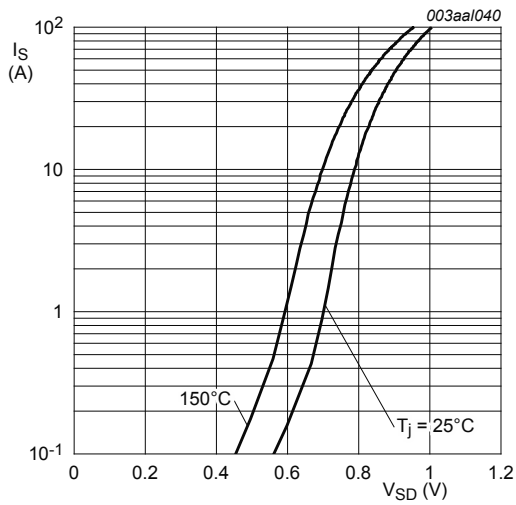


Fig. 15. Source current as a function of source-drain voltage; typical values

$$V_{GS} = 0\text{V}$$

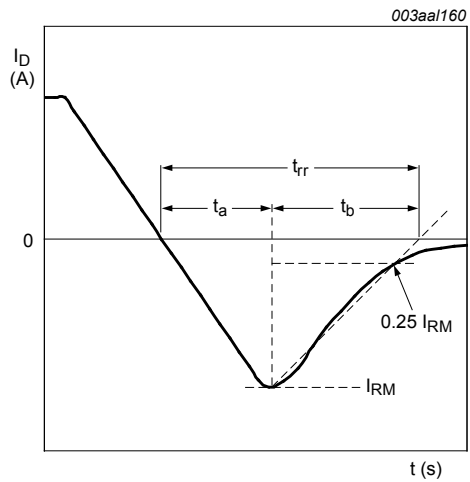


Fig. 16. Reverse recovery timing definition

11. Package outline

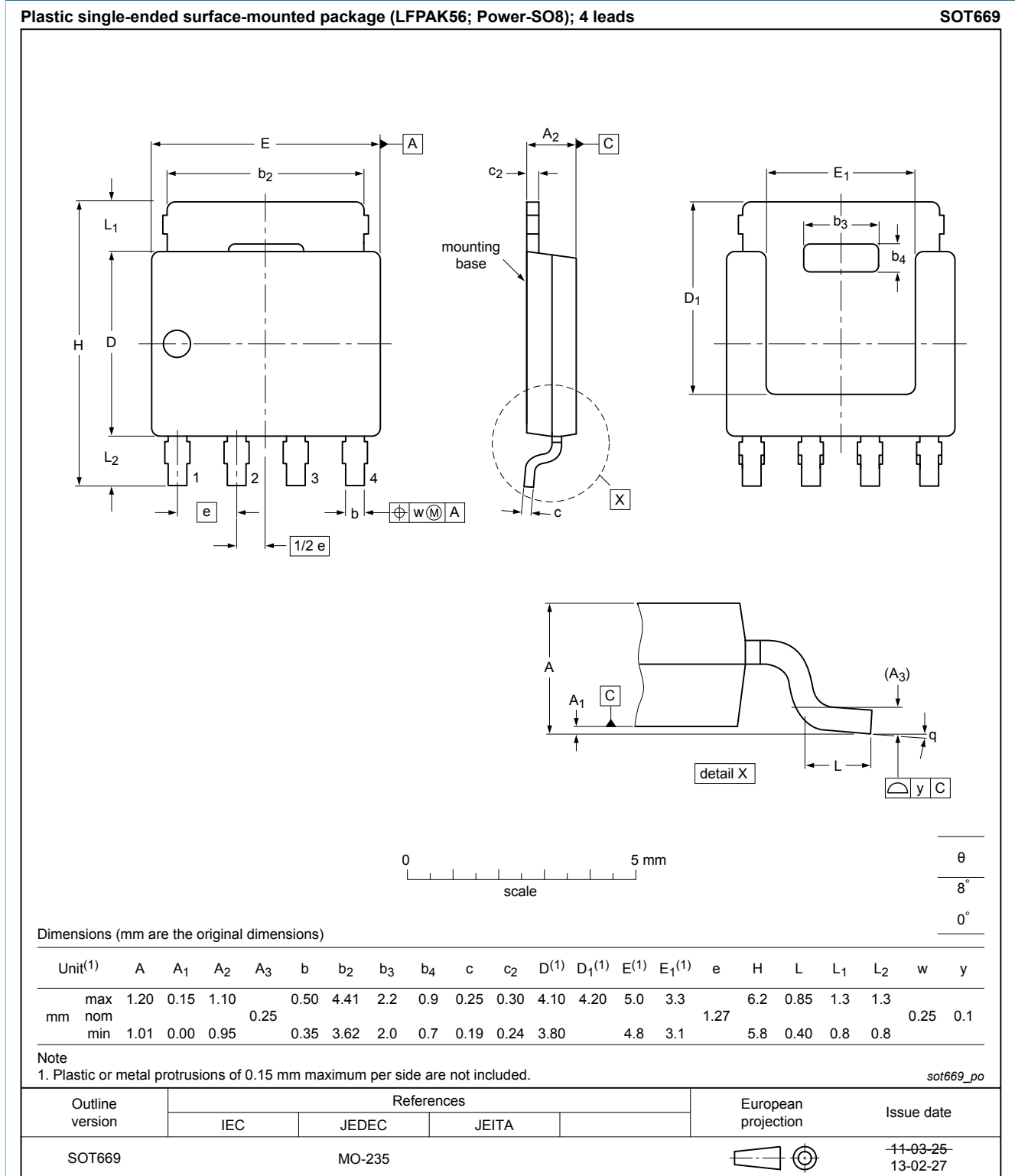


Fig. 17. Package outline LPAK56; Power-SO8 (SOT669)

N-channel 30 V, 4.0 mΩ logic level MOSFET in LPAK56 using NextPowerS3 Technology

12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nexperia.com>.

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N-channel 30 V, 4.0 mΩ logic level MOSFET in LPAK56 using NextPowerS3 Technology

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